

## **LISTING OF CLAIMS**

Please cancel, without prejudice, claim 24. The claims are unchanged from the previously submitted Amendment:

1-18. (Cancelled.)

19.(Previously Presented) A method for programming a voltage threshold ( $V_t$ ) level of a core cell in a memory device, the method comprising steps of:

determining a desired  $V_t$  for the core cell;

programming a portion of the  $V_t$  of the core cell using a selected programming strength;

verifying that the portion of the  $V_t$  is successfully programmed;

adjusting the selected programming strength; and

repeating the step of programming, verifying, and adjusting until the  $V_t$  of the core cell is substantially equal to the desired  $V_t$ .

20.(Previously Presented) The method of claim 19, further comprising, after the step of verifying, a step of returning to the step of programming using the selected programming strength if it is determined that the portion of the  $V_t$  was unsuccessfully programmed.

21.(Previously Presented) The method of claim 20, wherein the step of adjusting is a step of weakening the selected programming strength.

22.(Previously Presented) The method of claim 20, wherein the step of adjusting is a step of weakening the selected programming strength as the  $V_t$  of the core cell approaches the desired  $V_t$ .

23.(Previously Presented) The method of claim 20, wherein the step of adjusting is a step of weakening the selected programming strength after each successful steep of verifying.

24. (Cancelled.)